

***EB4030DTSI-P* MEMS Microphone IC**

Product Description

The ***EB4030DTSI-P*** microphone IC are integrated with specialized pre-amplification ASIC to provide high sensitivity, high SNR output from a capacitive audio sensor. It's packaged for surface mounting and high temperature reflow assembly. ***EB4030DTSI-P*** which is able to endure reflow temperature up to 260°C for 30 seconds can be used in SMT process. It is widely used in telecommunication and electronics device such as TV, Smart Speaker.

Features

- Top port
- High stability - no risk of membrane aging
- Suitable for automatic pick-and-place handler and SMT process
- Miniature dimension 4.00mm x 3.00mm x 1.00mm
- Low current consumption 80uA
- RoHS/Green compliant
- Sensitivity deviation within $\pm 1\text{dB}$
- Package type : LGA 8-pin
- Omnidirectional

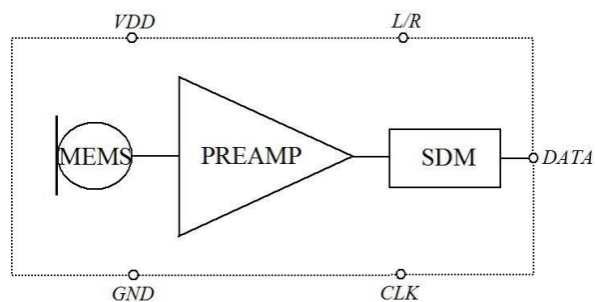
Applications

- TVs
- Smart Speakers
- IoT Devices

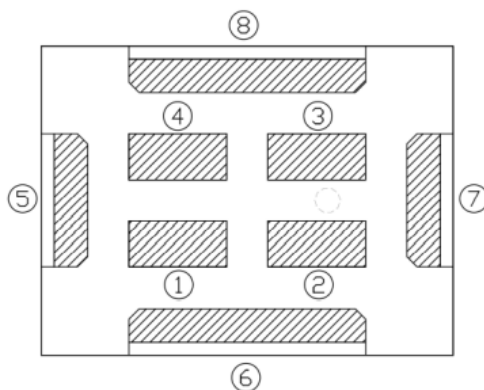
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Functional Block Diagram



Pin Definition and Function



Bottom View

Table 1

Pin #	Symbol	Type	Function
1	DATA	Digital O	Digital Output Signal
2	CLK	Digital I	Clock Input to Microphone
3	L/R	Non-Digital I	Left(Low) / Right(High) Select Pin
4	VDD	Power	Power Supply
5	GND	Power	Ground
6	GND	Power	Ground
7	GND	Power	Ground
8	GND	Power	Ground

Temperature Range

Table 2

Storage Temperature	T _{STG}	-40°C ~ 125°C
Operating Temperature Range	T _A	-40°C ~ 105°C

Acoustical and Electrical Characteristics

Table 3 Typical test conditions are $T_A = 23\text{ }^{\circ}\text{C}$, $V_{DD} = 1.8\text{ V}$ and $R.H. = 50\%$ measured in a pressure chamber test setup. All voltages refer to GND node

Parameters	Symbol	Min.	Typ	Max.	Unit	Test Conditions
Low Frequency Roll-off	LFRO		50		Hz	-3dB relative to 1KHz
Supply Voltage	Vdd	1.6		3.6	V	
Output Load	C _{Load}			100	pF	
Wake-up Time ⁽¹⁾			100		ms	Fclk $\geq$ 1MHz
Startup Time			100		ms	
Sleep Time			1		ms	Fclk $\leq$ 1KHz
Data Format	1/2 Cycle PDM					
Directivity	Omnidirectional					
Polarity	Increasing density of 1's					Increasing sound pressure

Table 4. Performance Mode Microphone Specifications Typical test conditions are $T_A = 23\text{ }^{\circ}\text{C}$, $V_{DD} = 1.8\text{V}$, Clock=2.4MHz and $R.H. = 50\%$ measured in a pressure chamber test setup. All voltages refer to GND node

Parameters	Symbo	Min.	Typ.	Max.	Unit	Test Conditions
Acoustic						
Sensitivity	S	-27	-26	-25	dBFS	1KHz, 94dBSPL
Signal to Noise Ratio	S/N		64		dBA	A-weighted
Equivalent Noise Level	ENL	30			dBA	A-weighted
Total Harmonic Distortion	THD	<0.2			%	94dB SPL
		1			%	110dBSPL
Acoustic Overload Point	AOP	120			dB SPL	10% THD@1KHz, S = Typ.
Electrical						
Clock Frequency	Fclk	1.0		4.8	MHz	
Current Consumption	Isb		550		μA	Vdd=1.8V
			850		μA	Vdd=3.6V
Power Supply Rejection Ratio	PSRR		60		dBV/FS	1KHz, 200 mV peak to peak sinewave
Power Supply Rejection	PSR+N		-80		dBFS (A)	217Hz, 100mV 1/8 duty cycle peak to peak square wave superimposed on Vcc 2.1V, A-weighted

Table 5. Low-Power Mode Microphone Specifications

Typical test conditions are TA = 23 °C, VDD = 1.8V, Clock=768KHz and R.H. = 50 % measured in a pressure chamber test setup. All voltages refer to GND node

Parameters	Symbo	Min	Typ	Max.	Unit	Test Conditions
Acoustic						
Sensitivity	S	-27	-26	-25	dBFS	1KHz, 94dBSPL
Signal to Noise Ratio	S/N		64		dBA	A-weighted
Equivalent Noise Level	ENL		30		dBA	A-weighted
Total Harmonic Distortion	THD		<0.2		%	94dBSPL
			1		dBSPL	110dBSPL
Acoustic Overload Point	AOP		120		dBSPL	10% THD@1KHz, S = Typ.
Electrical						
Clock Frequency	Fclk	350		800	KHz	
Current Consumption	Isb		300		μA	Vdd=1.8V
			400		μA	Vdd=3.6V
Power Supply Rejection Ratio	PSRR		60		dBV/FS	1KHz, 200 mV peak to peak sine wave
Power Supply Rejection	PSR+N		-80		dBFS (A)	217Hz, 100mV 1/8 duty cycle peak to peak square wave superimposed on Vcc 2.1V, A-weighted

Table 6. Sleep Mode Microphone Specifications

Typical test conditions are TA = 23 °C, VDD = 1.8V, Clock=0KHz and R.H. = 50 % measured in a pressure chamber test setup. All voltages refer to GND node

Parameters	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Clock Frequency	Fclk	0		250	KHz	
Current Consumption Sleep Mode	Isleep		10		μA	Clock = VDD or GND

(1). Time from the first clock edge to valid output data

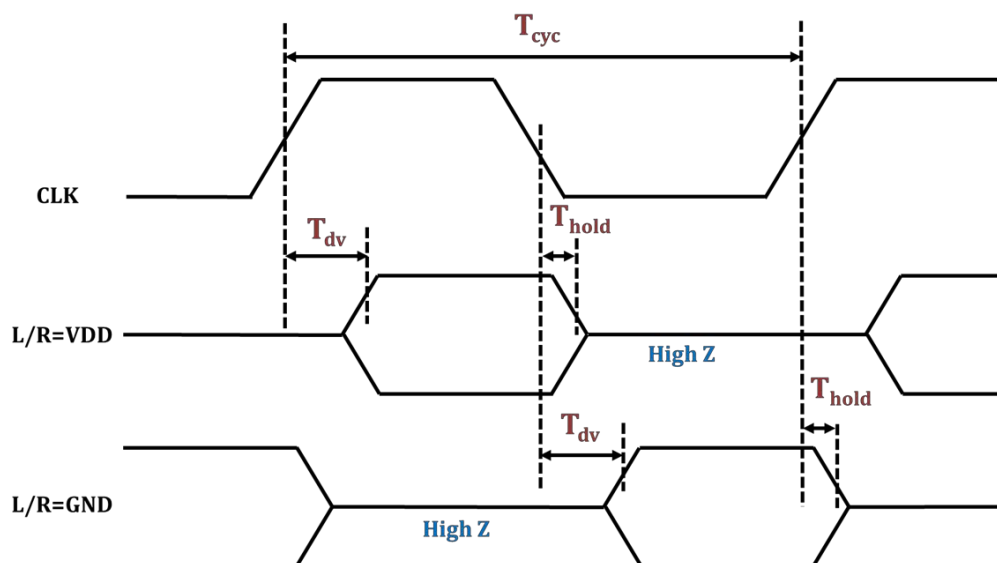
Timing Characteristics

Table 7. Microphone Interface Specifications

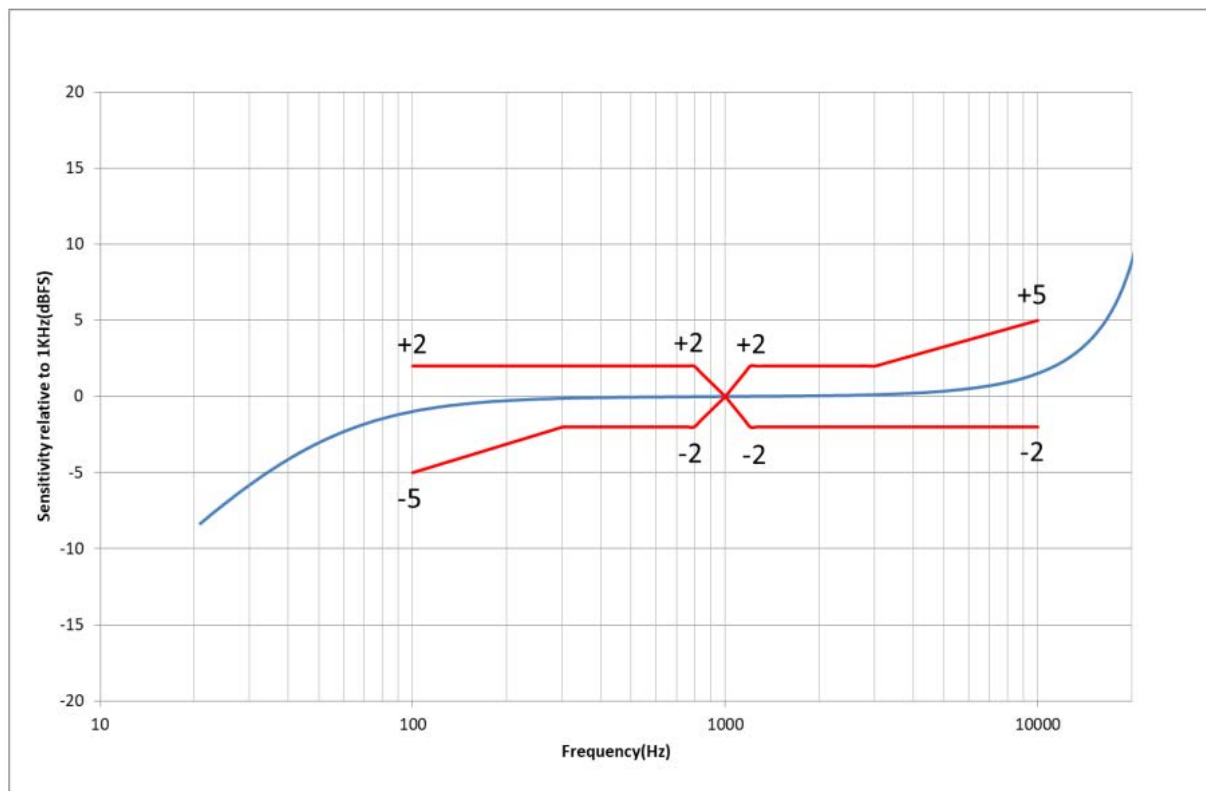
Parameters	Symbol	Min	Typ.	Max.	Unit	Test Conditions
Logic Input High	V_{IH}	$0.70 \times V_{DD}$		V_{DD}	V	
Logic Input Low	V_{IL}	-0.3		$0.35 \times V_{DD}$	V	
Logic Output High	V_{OH}	$0.65 \times V_{DD}$		V_{DD}	V	$I_{out} = 1mA$
Logic Output Low	V_{OL}	0		$0.35 \times V_{DD}$	V	$I_{out} = 1mA$
Clock Duty Cycle		40		60	%	
Clock Period for Normal Mode	T_{cyc}	308		1000	ns	
Data Setup Time	T_{dv}			$30^{(1)}$	ns	
Data Hold Time	T_{hold}	$3^{(1)}$			ns	

(1). Guaranteed by design

Timing Waveforms



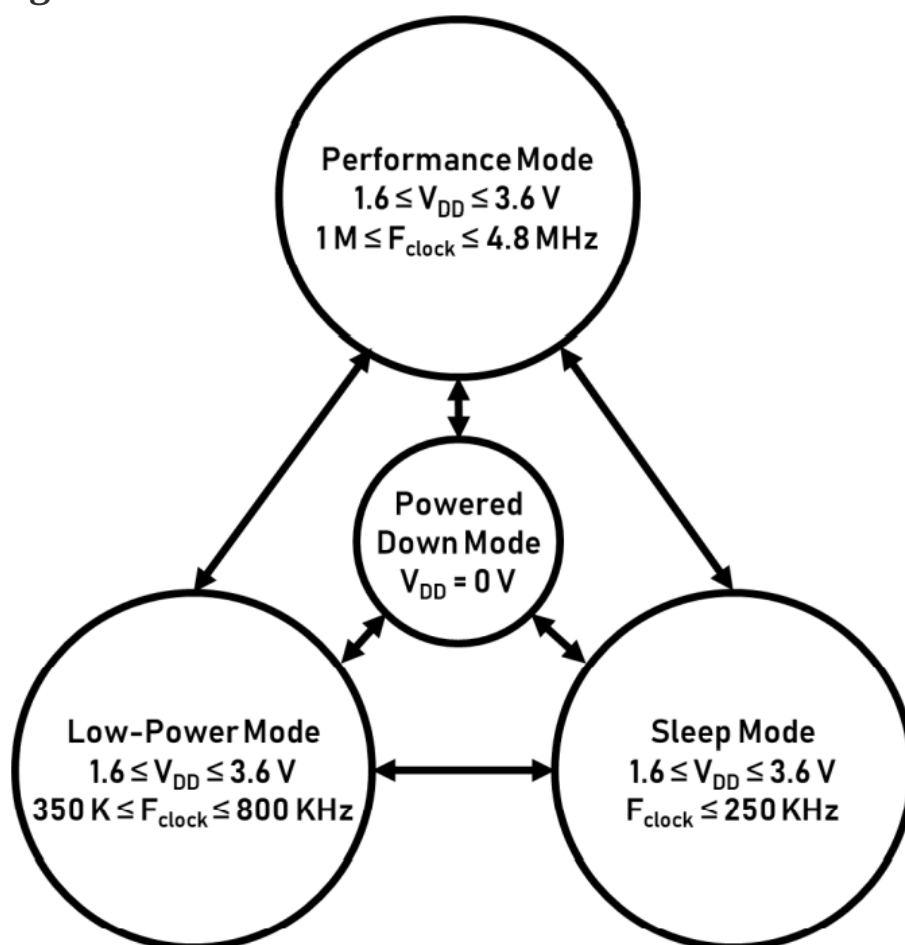
Frequency Response



* Measured frequency of 1 KHz

Upper Limit							
Hz	100	800	1000	1200	2000	3000	10000
dB ref. 1KHz	+2	+2	0	+2	+2	+2	+5
Lower Limit							
Hz	100	300	800	1000	1200	3000	10000
dB ref. 1KHz	-5	-2	-2	0	-2	-2	-2

State Diagram



Reliability Qualifications

Table 8.

Test Item	Description
High Temperature Storage	Storage at 105°C for 1,000 hours IEC 60068-2-2 Test Ba
Low Temperature Storage	Storage at -40°C for 1,000 hours IEC 60068-2-1 Test Aa
High Temperature Operation Bias	Under Bias at 105°C for , 1,000 hours IEC 60068-2-2 Test Ba
Low Temperature Operation Bias	Under Bias at -40°C for , 1,000 hours IEC 60068-2-1 Test Aa
Temperature Humidity Bias	Under Bias at 85°C/85%RH for 1,000 hours JESD22-A101-B
Thermal Shock	Thermal Shock 100 cycles from -40°C~100°C, 100 cycles IEC 60068-2-14
Reflow	3 reflow cycles with peak 260°C J-STD-020D
Vibration	4 cycles lasting 12 minutes from 20 to 2KHz in X, Y and Z with peak acceleration of 20G MIL 883E, Method 2007.2, A
Shock	3 pulses 10,000G in X,Y and Z IEC 60068-2-27, Test Ea
ESD	HBM:3KV, MM:300V, CDM:500V Air Discharge:12KV, Contact Discharg:8KV JESD22-A114(HBM); JESD22-A115(MM) JESD22-C101(CDM) IEC 61000-4-2(Air Discharge) IEC 61000-4-2(Contact Discharge)
Tumble Test	300 tumbles from a height of 1m onto a steel base.

Notes: Microphones meet all acoustic and electrical specifications before and after reliability testing, except sensitivity which can deviate up to 3dB.

After 3 reflow cycles, the sensitivity of the microphone shall not deviate more than 1 dB from its initial value

Reflow Profile

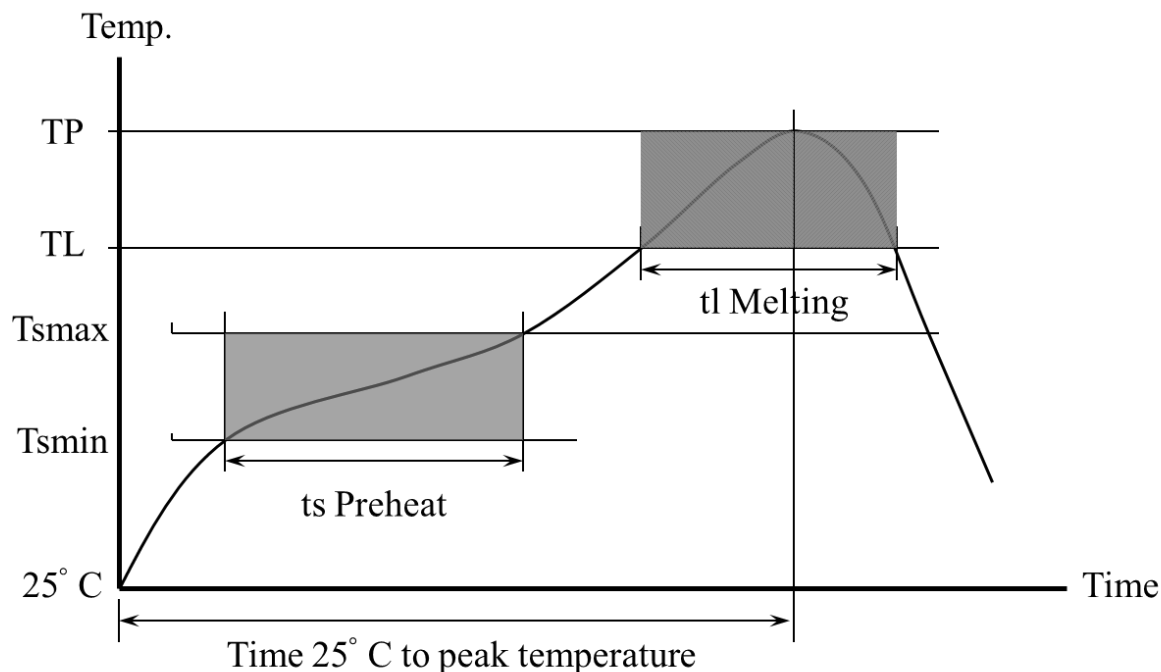


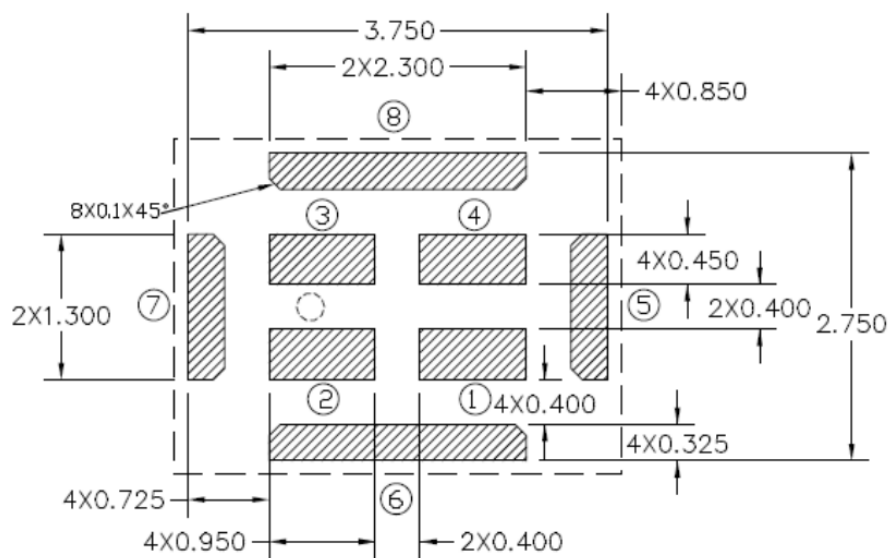
Table 9. Recommended Reflow Profile Limits

Profile Feature	Pb-free
Preheat	
Minimum temperature (Tsmmin)	150 °C
Maximum temperature (Tsmmax)	200 °C
Time (ts)	60~180 sec
Average Ramp up rate (Tsmmax to Tp)	3 °C/sec
Melting area	
Melting temperature (TL)	217 °C
Time maintained above melting (t)	60~150 sec
Peak Temperature (TP)	260 °C
Time within 5°C of actual peak temperature	
Ramp down rate	20~40 sec
Time 25°C to peak temperature	6 °C/sec maximum 8 minute maximum

Notes: Based on IPC/JDEC J-STD-020 Revision C.

All temperatures refer to topside of the package, measured on the package body surface

PCB Land Pattern Layout



Application Circuit

The L/R digital pad lets the user to select the DATA signal pattern as explained in Table 6. The L/R pin must be connected to either VDD or GND.

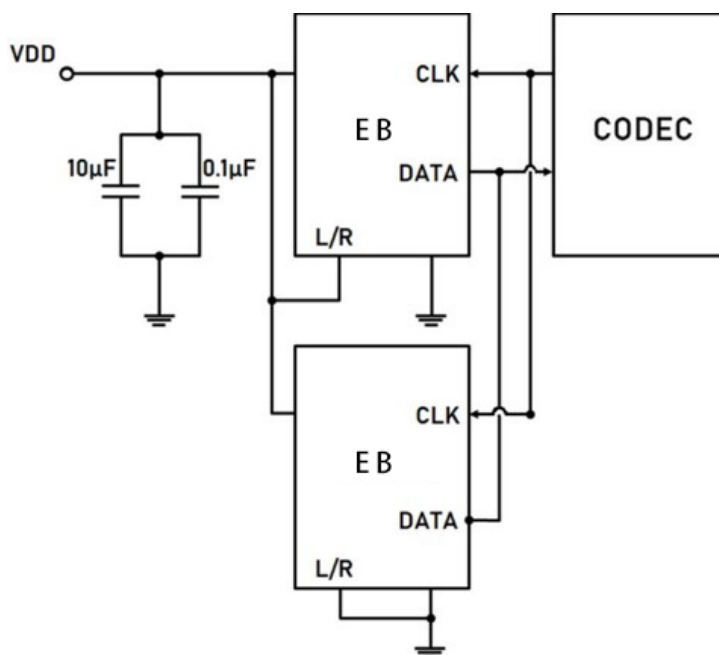
Table 10. L/R channel selection

L/R	CLK low	CLK high
GND	DATA valid	High impedance
VDD	High impedance	DATA valid

Single microphone application:

0.1 μ F ceramic, and 10 μ F ceramic power supply decoupling capacitors should be placed as near as possible to VDD of the device. **The L/R pin must be connected to VDD or GND.**

Two microphones application:



Handling Instructions

The MEMS microphone IC can be handled using standard pick-and-place and chip shooting equipment. Care should be taken to avoid damage to the MEMS microphone IC structure as follows:

- . Do not apply vacuum nozzle over the acoustic port (AP) of the microphone to avoid damage to the device.
- . Do not blow air directly into acoustic port.
- . Brushing the board with/without solvents may damage the device.
- . Do not use excessive force to place the microphone on the PCB.
- . In case of manual handling, it should be handled with plastic tweezers to avoid damage the device.

Dimensions

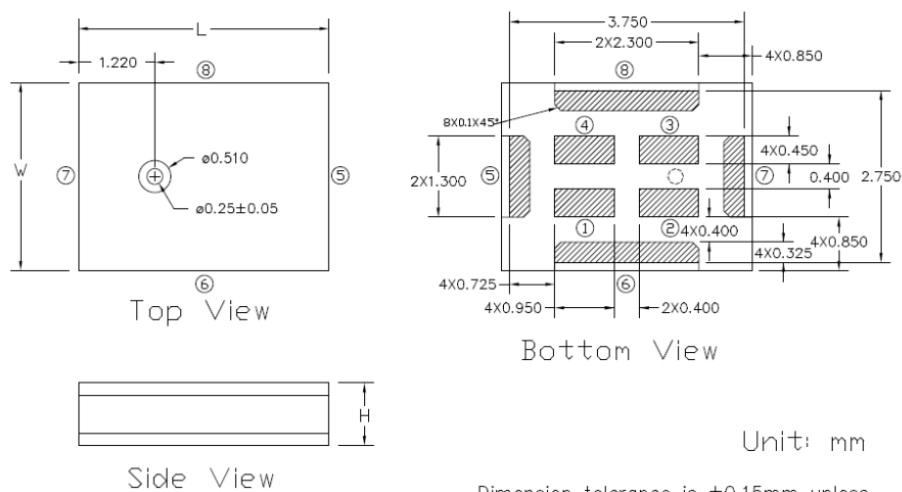
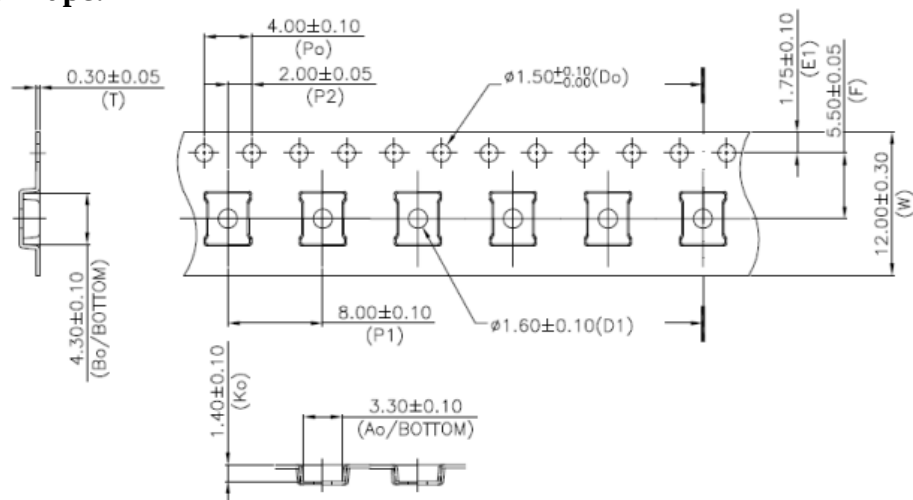


Table 11. (Top View)

Item	Dimension	Tolerance
Length (L)	4.00 mm	± 0.10 mm
Width (W)	3.00 mm	± 0.10 mm
Height (H)	1.00 mm	± 0.10 mm
Acoustic Port	$\Phi 0.25$ mm	± 0.05 mm

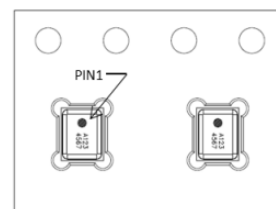
Package Information

Carrier Tape:

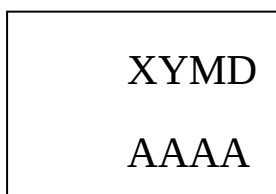


Unit: mm

1. 10 sprocket hole pitch cumulative tolerance ± 0.20 .
2. Carrier camber is within 1 mm in 250 mm.
3. Material : Black Conductive Polystyrene Alloy.
4. All dimensions meet EIA-481 requirements.
5. Thickness : 0.30 ± 0.05 mm.
6. MSL(Moisture sensitivity level) Class1.



Laser Marking:



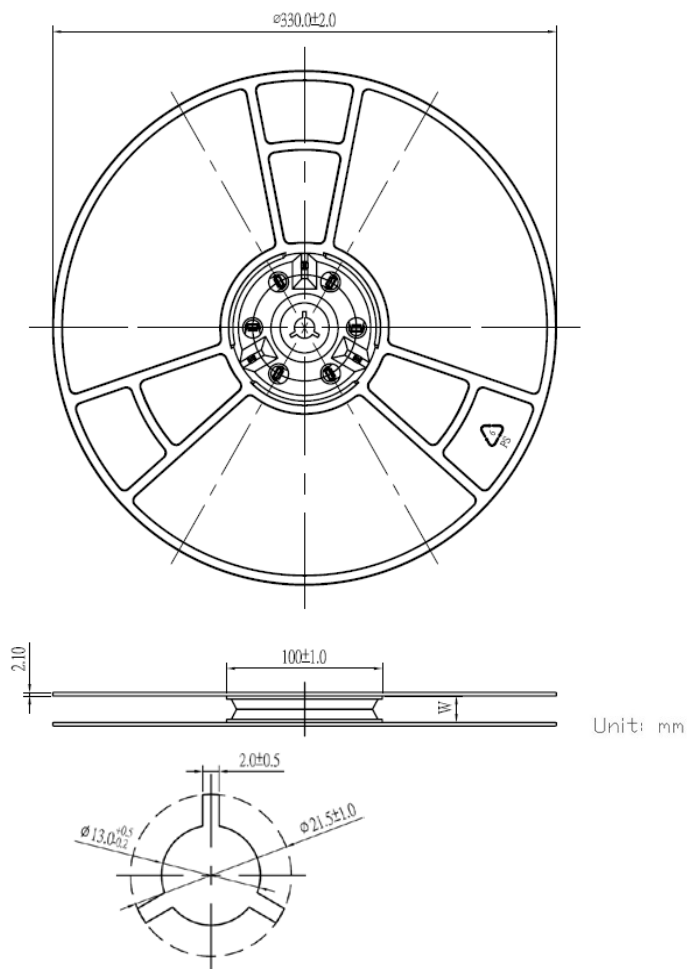
Laser marking on the top side

XYMD	Internal Tracking Code(X:Subject to change without notice) Date Code(Y:Year; M:Month; D:Day)
AAAA	Lot Tracking Code

13" Tape Reel :

Version 1.1
Date: 2022-01-19

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Model Number	Reel Diameter	Quantity Per Reel
EB4030DTSI-P	13"	5,000

Revision History

Version 1.1
Date: 2022-01-19

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Revision	Date	Description
1.0	2021/07/12	Formal release
1.1	2022/01/19	Modify “Acoustical and Electrical Characteristics” Modify “Timing Characteristics” Modify “State Diagram”